

<b>SANYO</b>	No. 1872A	<b>DRA2T</b>
		Silicon Planar Type
<b>2.0A Reverse Blocking Thyristor</b>		

**Features**

- TO202 package facilitating easy mounting
- Peak OFF-state (reverse) voltage : - 100 to - 600V
- Average ON-state current : 2A

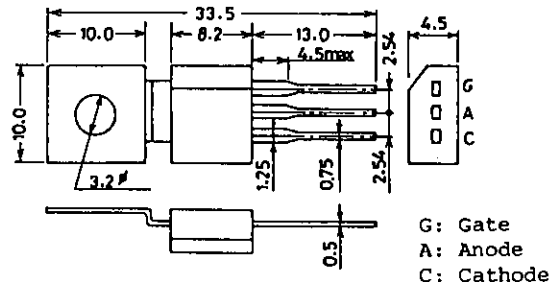
**Absolute Maximum Ratings at Ta = 25°C**

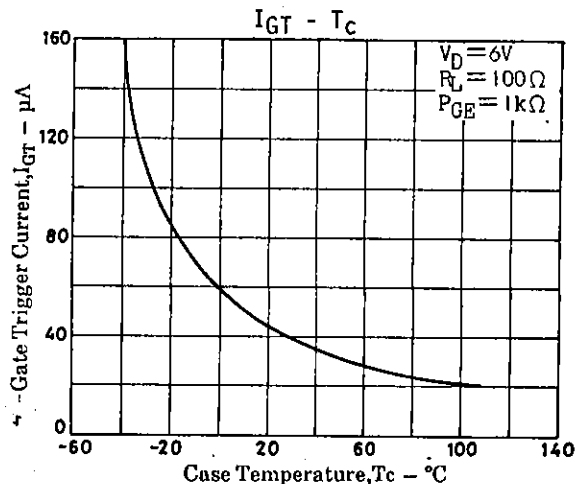
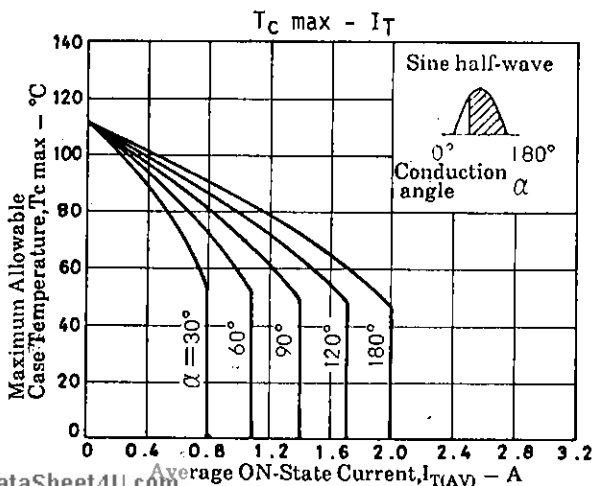
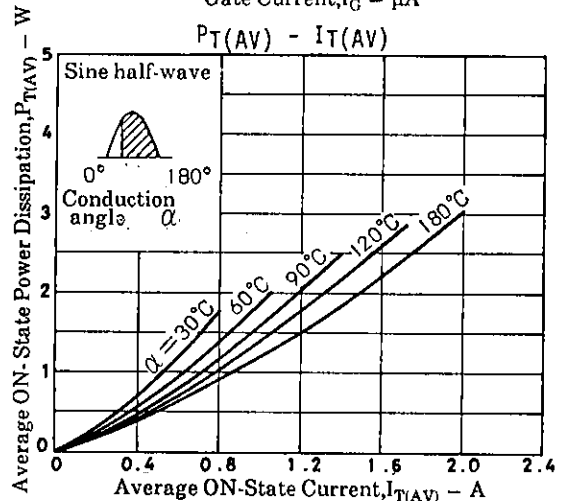
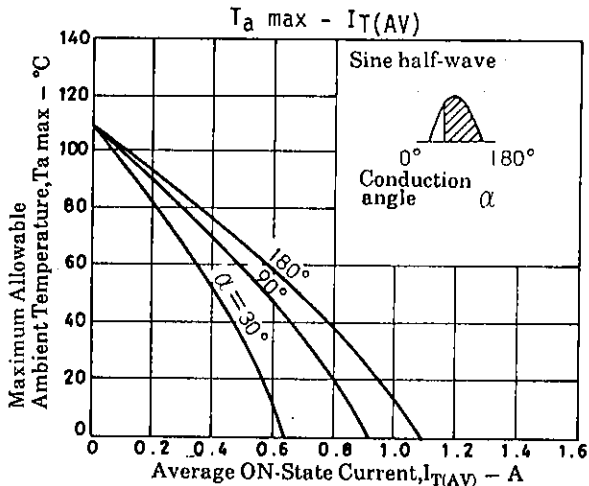
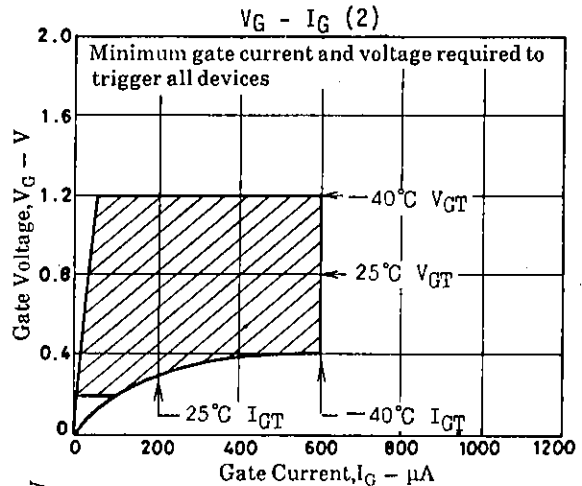
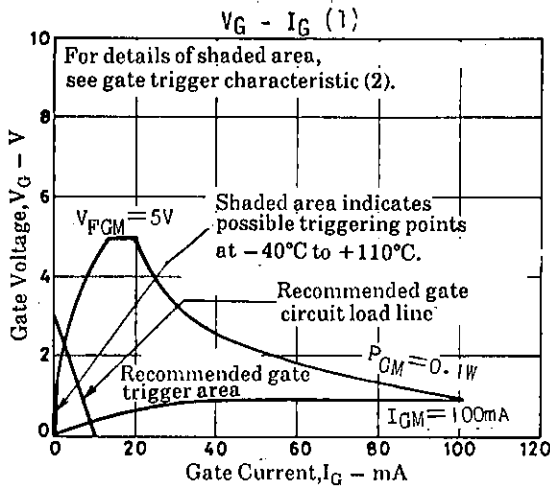
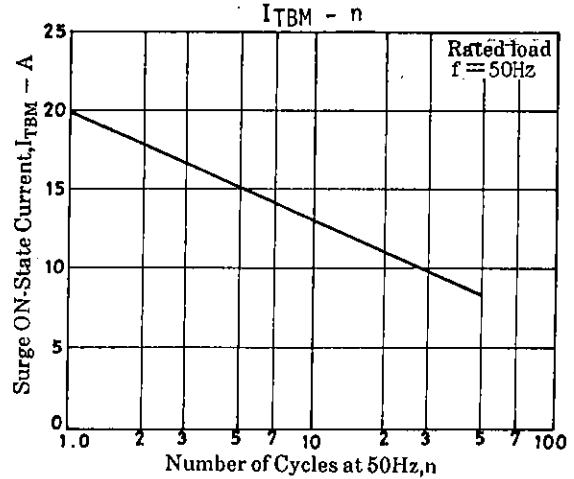
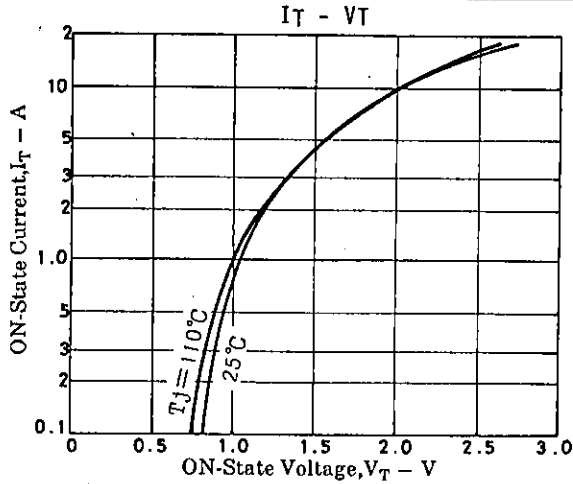
			DRA2TB	DRA2TC	DRA2TE	DRA2TG	unit
Repetitive Peak OFF-State Voltage	$V_{DRM}$	$R_{GK} = 1k\Omega$	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	$R_{GK} = 1k\Omega$	-150	-300	-500	-720	V
Repetitive Peak Reverse Voltage	$V_{RRM}$	$R_{GK} = 1k\Omega$	-100	-200	-400	-600	V
Average ON-State Current	$I_{T(AV)}$	$T_c = 45^\circ C$ , single-phase half-wave	→	→	→	2	A
Surge ON-State Current	$I_{TSM}$	Sine half-wave 1 cycle, 50Hz	→	→	→	20	A
Amperes Squared-Seconds	$\int i^2 T \cdot dt$	$1ms \leq t \leq 10ms$	→	→	→	1.6	A <sup>2</sup> s
Peak Gate Power Dissipation	$P_{GM}$	$f \geq 50Hz, duty \leq 10\%$	→	→	→	0.1	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	→	0.01	W
Peak Gate Forward Current	$I_{FGM}$	$f \geq 50Hz, duty \leq 10\%$	→	→	→	0.1	A
Peak Gate Reverse Voltage	$V_{RGM}$		→	→	→	-5	V
Junction Temperature	$T_j$		→	→	→	110	°C
Storage Temperature	$T_{stg}$		→	→	→	-40 to +110	°C
Weight			→	→	→	1.5	g

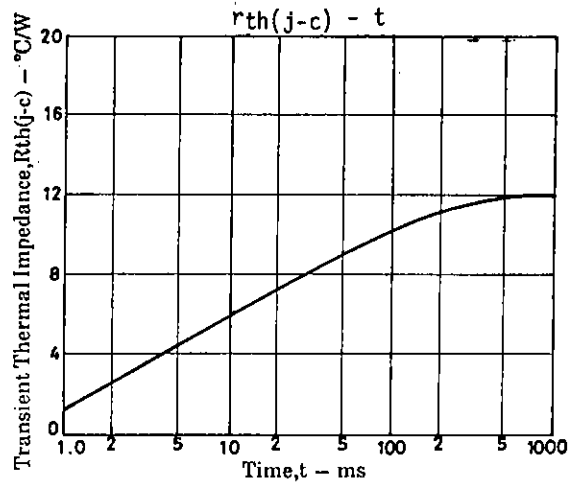
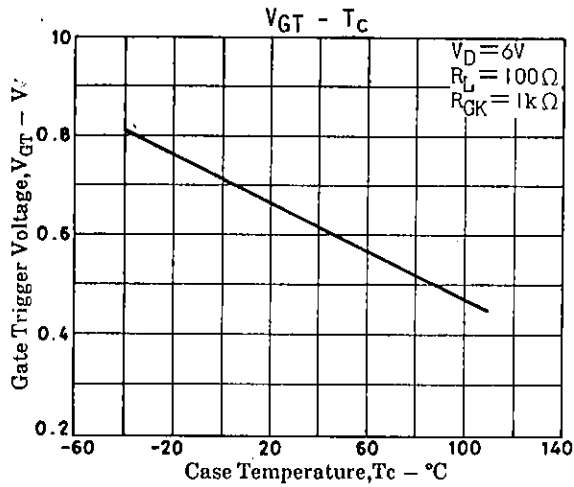
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Repetitive Peak OFF-State Current	$I_{DRM}$	$T_j = 110^\circ C, V_D = V_{DRM}, R_{GK} = 1k\Omega$			0.2	mA
Repetitive Peak Reverse Current	$I_{RRM}$	$T_j = 110^\circ C, V_R = V_{RRM}, R_{GK} = 1k\Omega$			-0.2	mA
Peak ON-State Voltage	$V_{TM}$	$I_{TM} = 10A$			2.0	V
Critical Rate of Rise of OFF-State Voltage	$dv/dt$	$T_j = 110^\circ C, V_D = V_{DRM}, R_{GK} = 1k\Omega$		15		V/ $\mu s$
Holding Current	$I_H$	$V_D = 24V, R_{GK} = 1k\Omega$		3.0		mA
Gate Trigger Current	$I_{GT}$	$V_D = 6V, R_L = 100\Omega, R_{GK} = 1k\Omega$			0.2	mA
Gate Trigger Voltage	$V_{GT}$	$V_D = 6V, R_L = 100\Omega, R_{GK} = 1k\Omega$			0.8	V
Gate Nontrigger Voltage	$V_{GD}$	$T_c = 110^\circ C, V_D = \text{Rated voltage}, R_{GK} = 1k\Omega$	0.2			V
Thermal Resistance	$R_{th(j-c)}$				12	°C/W

**Package Dimensions 1150**  
(unit: mm)







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